

Description

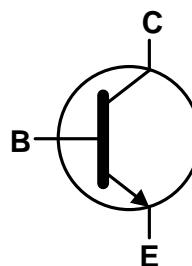
This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirement of Automotive Applications.

Features

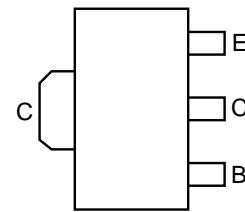
- $BV_{CEO} > 75V$
- $I_C = 3A$ High Continuous Current
- $I_{CM} = 10A$ Peak Pulse Current
- High Gain Holds up $h_{FE} > 300$ @ $I_C=1A$
- Low Equivalent On-Resistance; $R_{CE(SAT)} = 78m\Omega$ at 4.5A
- Excellent h_{FE} Characteristics up to 10A
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**



Top View



Device Symbol



Top View
Pin-Out

Ordering Information (Notes 4 and 5)

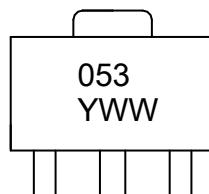
Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
FCX1053AQTA	053	7	12	1,000

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
5. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

SOT89



053 = Product Type Marking Code
YWW = Date Code Marking
Y = Last Digit of Year (ex: 7 = 2017)
WW = Week Code (01 to 53)

Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	150	V
Collector-Emitter Voltage	V_{CEO}	75	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	I_C	3	A
Base Current	I_B	500	mA
Peak Pulse Current	I_{CM}	10	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

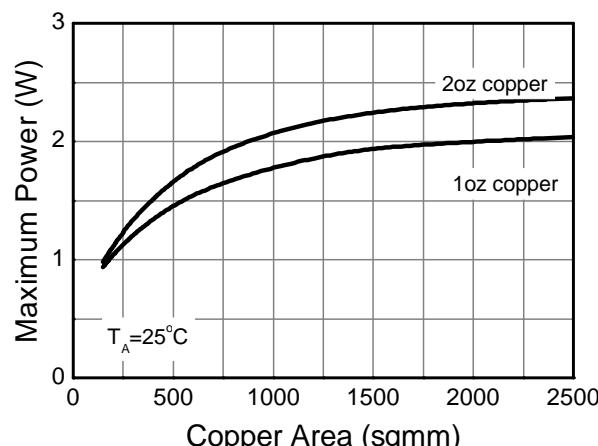
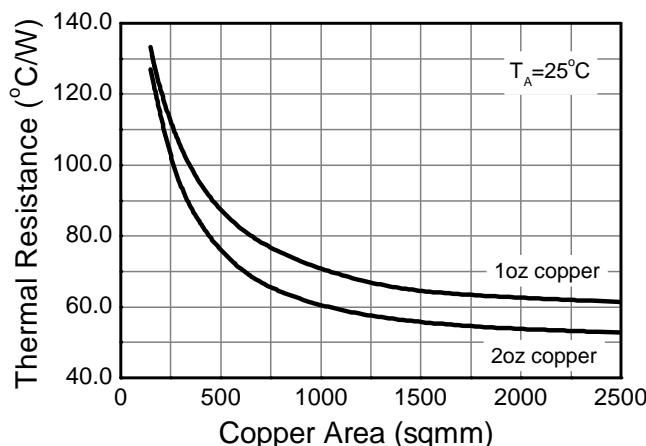
Characteristic	Symbol	Value	Unit
Power Dissipation	P_D	1	W
		1.6	
		2.0	
Thermal Resistance, Junction to Ambient Air	$R_{\theta JA}$	125	°C/W
		78	
		62.5	
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	3.6	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

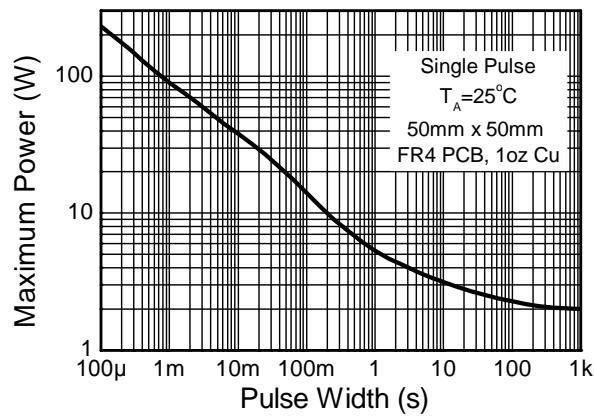
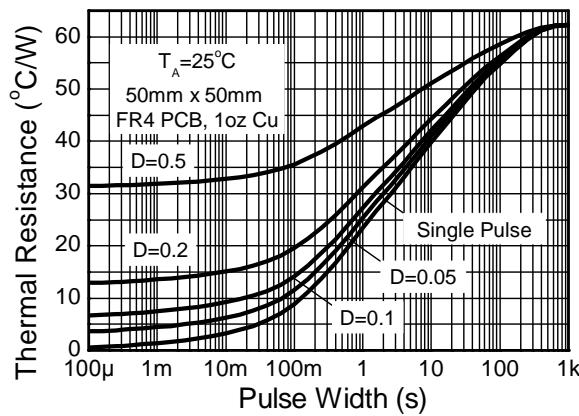
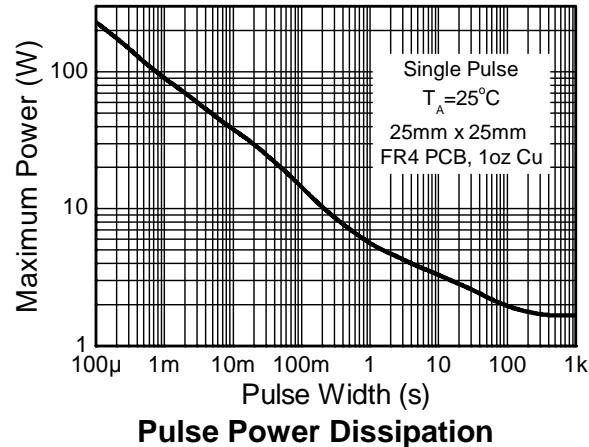
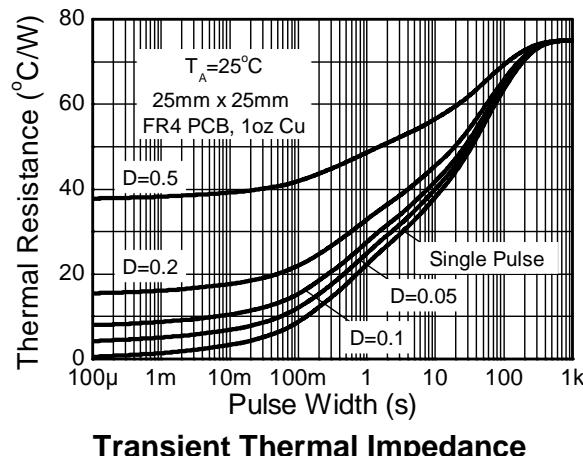
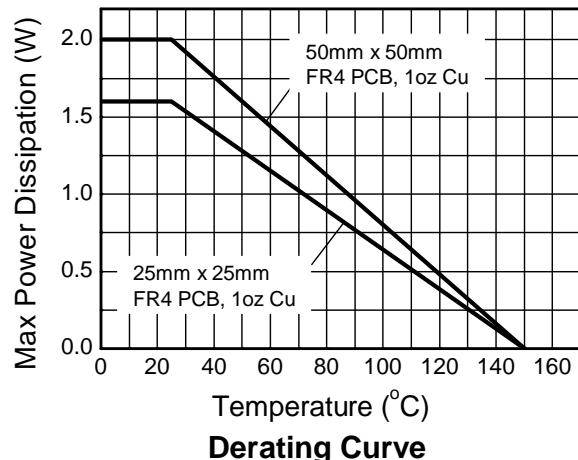
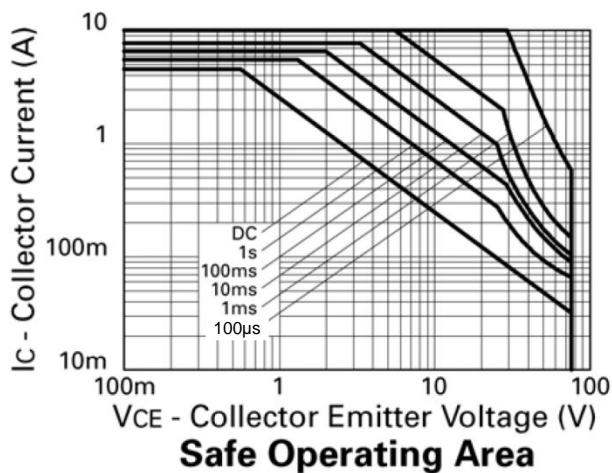
ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

Notes:

6. For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
7. Same as note 6, except the device is mounted on 25mm x 25mm 1oz copper.
8. Same as note 6, except the device is mounted on 50mm x 50mm 1oz copper.
9. Thermal resistance from junction to solder-point (on the exposed collector pad).
10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information


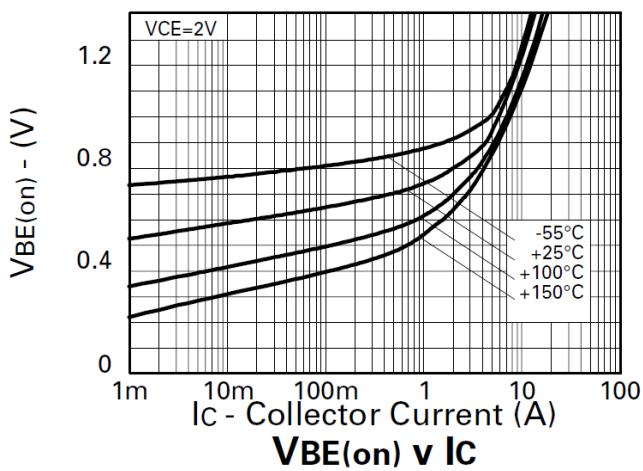
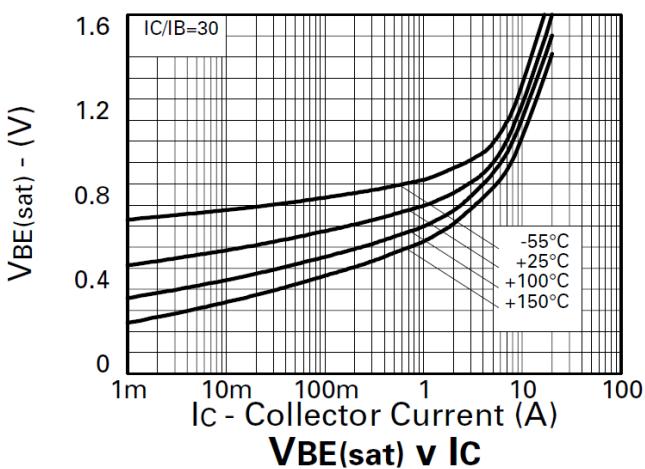
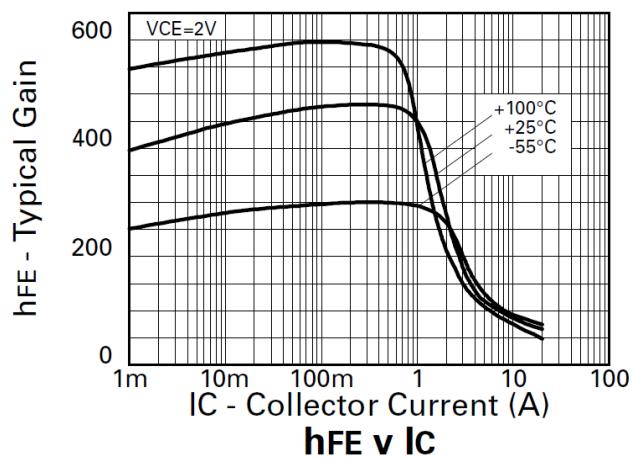
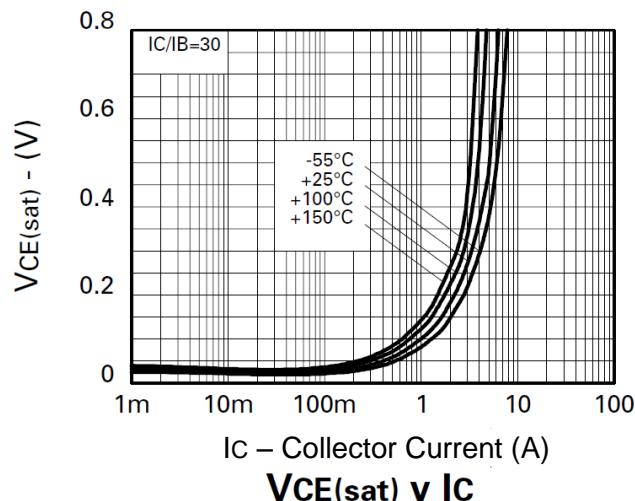
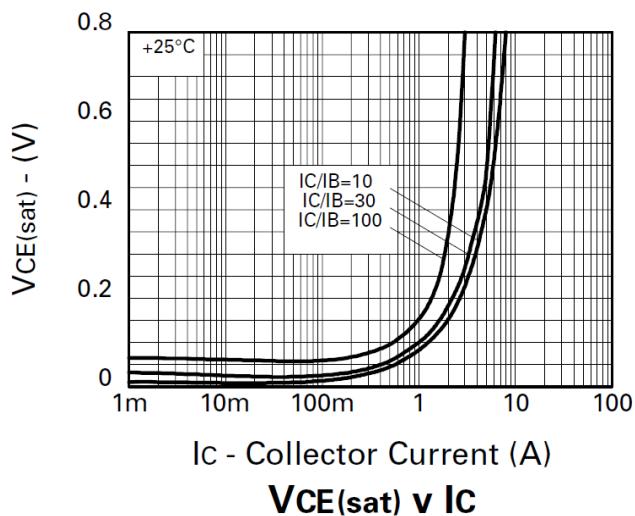


Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	150	250	—	V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage	BV_{CES}	150	250	—	V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage (Note 11)	BV_{CEO}	75	100	—	V	$I_C = 10\text{mA}$
Collector-Emitter Breakdown Voltage	BV_{CEV}	150	250	—	V	$I_C = 100\mu\text{A}, V_{\text{EB}} = 1\text{V}$
Emitter-Base Breakdown Voltage	BV_{EBO}	7	8.8	—	V	$I_E = 100\mu\text{A}$
Collector Cutoff Current	I_{CBO}	—	0.9	50	nA	$V_{\text{CB}} = 120\text{V}$
Collector Cutoff Current	I_{CES}	—	1.5	50	nA	$V_{\text{CES}} = 120\text{V}$
Emitter Cutoff Current	I_{EBO}	—	0.3	20	nA	$V_{\text{EB}} = 5.6\text{V}$
DC Current Transfer Static Ratio (Note 11)	h_{FE}	270 300 300 40 —	440 450 450 60 20	— 1200 — — —	—	$I_C = 10\text{mA}, V_{\text{CE}} = 2\text{V}$ $I_C = 0.5\text{A}, V_{\text{CE}} = 2\text{V}$ $I_C = 1\text{A}, V_{\text{CE}} = 2\text{V}$ $I_C = 4.5\text{A}, V_{\text{CE}} = 2\text{V}$ $I_C = 10\text{A}, V_{\text{CE}} = 2\text{V}$
Collector-Emitter Saturation Voltage (Note 11)	$V_{\text{CE}(\text{SAT})}$	—	21 55 150 160 350	30 75 200 210 440	mV	$I_C = 0.2\text{A}, I_B = 20\text{mA}$ $I_C = 0.5\text{A}, I_B = 20\text{mA}$ $I_C = 1\text{A}, I_B = 10\text{mA}$ $I_C = 2\text{A}, I_B = 100\text{mA}$ $I_C = 4.5\text{A}, I_B = 200\text{mA}$
Base-Emitter Saturation Voltage (Note 11)	$V_{\text{BE}(\text{SAT})}$	—	900	1000	mV	$I_C = 3\text{A}, I_B = 100\text{mA}$
Base-Emitter Turn-on Voltage (Note 11)	$V_{\text{BE}(\text{ON})}$	—	825	950	mV	$I_C = 3\text{A}, V_{\text{CE}} = 2\text{V}$
Transitional Frequency	f_T	—	140	—	MHz	$I_C = 50\text{mA}, V_{\text{CE}} = 10\text{V}, f = 100\text{MHz}$
Output Capacitance	C_{obo}	—	21	30	pF	$V_{\text{CB}} = 10\text{V}, f = 1\text{MHz}$
Switching Time	t_{ON}	—	162	—	ns	$V_{\text{CC}} = 50\text{V}, I_C = 2\text{A}, I_{B1} = -I_{B2} = \pm 20\text{mA}$
	t_{OFF}		900		ns	

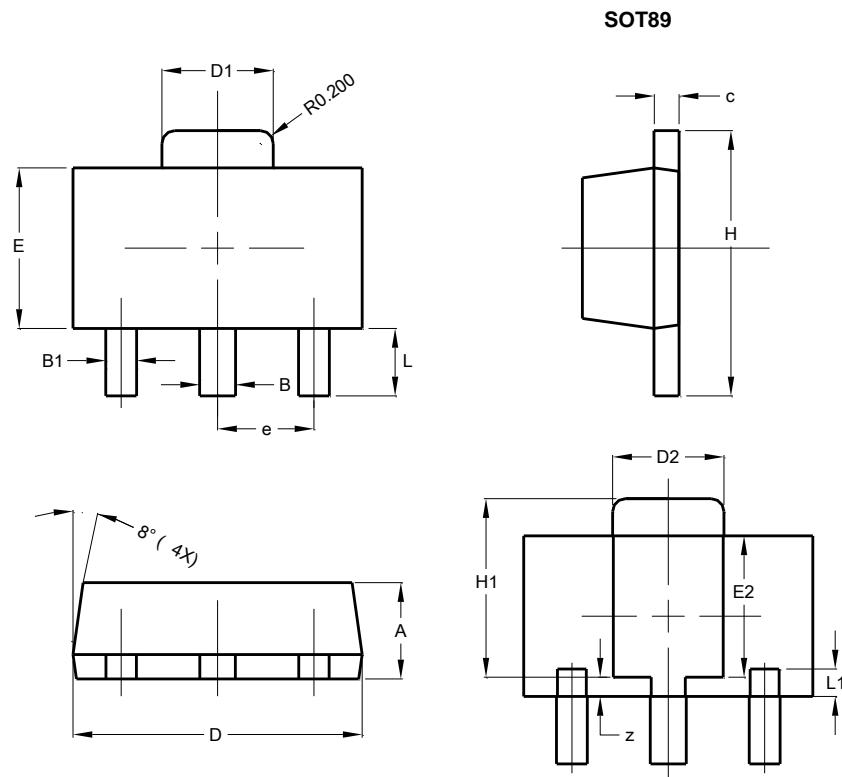
Note: 11. Measured under pulsed conditions. Pulse width = 300 μs . Duty cycle $\leq 2\%$.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

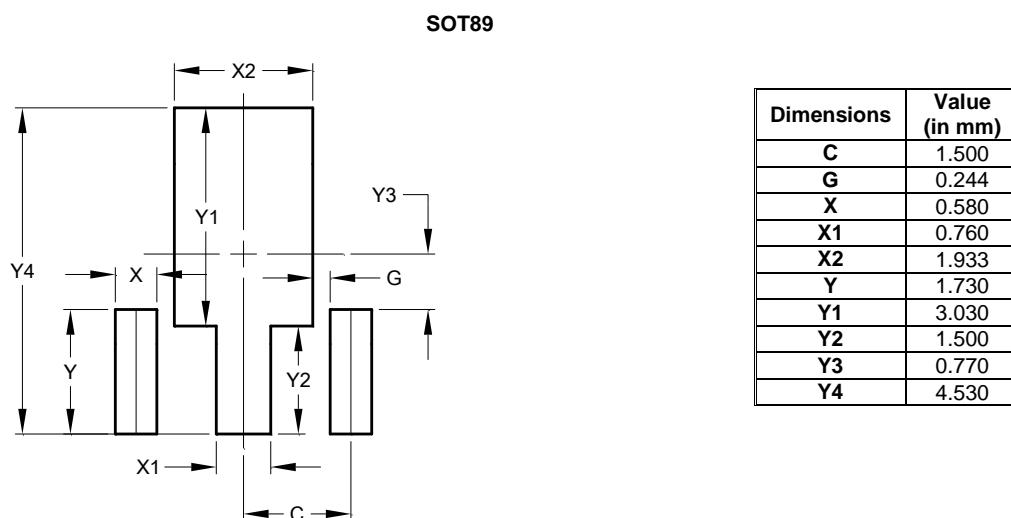


SOT89			
Dim	Min	Max	Typ
A	1.40	1.60	1.50
B	0.50	0.62	0.56
B1	0.42	0.54	0.48
c	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.62	1.83	1.733
D2	1.61	1.81	1.71
E	2.40	2.60	2.50
E2	2.05	2.35	2.20
e	-	-	1.50
H	3.95	4.25	4.10
H1	2.63	2.93	2.78
L	0.90	1.20	1.05
L1	0.327	0.527	0.427
z	0.20	0.40	0.30

All Dimensions in mm

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



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